

# 2MBI200VA-060-50

**IGBT Modules** 

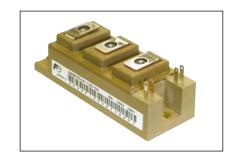
# IGBT MODULE (V series) 600V / 200A / 2 in one package

#### ■ Features

High speed switching Voltage drive Low Inductance module structure

#### Applications

Inverter for Motor Drive AC and DC Servo Drive Amplifier Uninterruptible Power Supply Industrial machines, such as Welding machines



#### **■** Maximum Ratings and Characteristics

● Absolute Maximum Ratings (at T<sub>c</sub>=25°C unless otherwise specified)

Items			Conditions		Maximum ratings	Units	
Collector-Emitter voltage		Vces		,	600	V	
Gate-Emitter voltage		V <sub>GES</sub>			±20	V	
Collector current		Ic	Continuous	Tc=100°C	200		
		I <sub>C pulse</sub>	1ms		400	۸	
		-Ic				Α	
		-I <sub>C pulse</sub>	1ms	,	400		
Collector power dissipation		Pc	1 device		650		
Junction temperature		T <sub>j</sub>			175		
Operating junction temperature (under switching conditions)		T <sub>jop</sub>			150	°C	
Case temperature		Tc			125		
Storage temperature		T <sub>stg</sub>		,	-40 ~ 125		
Isolation voltage   between terminal and copper base (*1)		Viso	AC: 1min.		2500	VAC	
Screw torque	Mounting (*2)	-			5.0	N m	
	Terminals (*3)	-			5.0	IN III	

Note \*1: All terminals should be connected together when isolation test will be done.

Note \*2: Recommendable Value : 3.0-5.0 Nm (M5 or M6) Note \*3: Recommendable Value : 2.5-3.5 Nm (M5)

■ Electrical characteristics (at T<sub>i</sub>= 25°C unless otherwise specified)

lama	Cumbala	Conditions		Characteristics			Heite
Items	Symbols			min.	typ.	max.	Units
Zero gate voltage collector current	Ices	V <sub>GE</sub> = 0V, V <sub>CE</sub> = 600V		-	-	1.0	mA
Gate-Emitter leakage current	-Emitter leakage current $I_{GES}$ $V_{CE} = 0V, V_{GE} = \pm 20V$		-	-	200	nA	
Gate-Emitter threshold voltage	V <sub>GE (th)</sub>	$V_{CE} = 20V, I_{C} = 200mA$		6.2	6.7	7.2	V
	V <sub>CE (sat)</sub>	V <sub>GE</sub> = 15V I <sub>C</sub> = 200A	T <sub>j</sub> =25°C	-	1.80	2.25	V
	(terminal)		T <sub>j</sub> =125°C	-	2.10	-	
Collector-Emitter saturation voltage			T <sub>j</sub> =150°C		2.30		
Conector-Emitter Saturation Voltage	V <sub>CE (sat)</sub> (chip)	V <sub>GE</sub> = 15V I <sub>C</sub> = 200A	T <sub>j</sub> =25°C	-	1.60	2.05	
			T <sub>j</sub> =125°C	-	1.90	-	
			T <sub>j</sub> =150°C		2.10		
Internal gate resistance	nce R <sub>G (int)</sub> -			-	4	-	Ω
Input capacitance	Cies	$V_{CE} = 10V, V_{GE} = 0V, f = 1W$	-	12.8	-	nF	
	ton	$V_{\text{CC}} = 300V$		-	650	-	nsec
Turn-on time	tr			-	300	-	
	t <sub>r (i)</sub>			-	100	-	
Turn-off time	toff			-	600	-	
Turn-on time	t <sub>f</sub>			-	40	-	
	VF	V <sub>GE</sub> = 0V I <sub>F</sub> = 200A	T <sub>j</sub> =25°C	-	1.70	2.15	V
	(terminal)		T <sub>j</sub> =125°C	-	1.60	-	
Forward on voltage	(terrillial)	IF - 200A	T <sub>j</sub> =150°C		1.57		
rorward on voltage	VF	V <sub>GE</sub> = 0V	T <sub>j</sub> =25°C	-	1.60	2.05	
		I <sub>F</sub> = 200A	T <sub>j</sub> =125°C	-	1.50	-	
	(chip)	IF - 200A	T <sub>j</sub> =150°C		1.47		
everse recovery time $t_{rr}$ $I_F = 200A$		-	200	-	nsec		

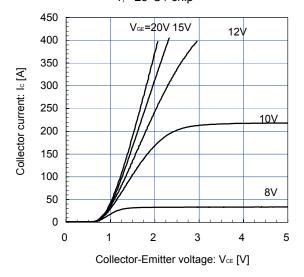
#### Thermal resistance characteristics

Items	Symbols	Conditions	Characteristics			Units
items		Conditions	min.	typ.	max.	Units
Thermal resistance (Aderrica)	Ь	IGBT	-	-	0.23	°C/W
Thermal resistance (1device)	R <sub>th(j-c)</sub>	FWD	-	-	0.41	
Contact thermal resistance (1device) (*4)	R <sub>th(c-f)</sub>	with Thermal Compound	-	0.050	-	

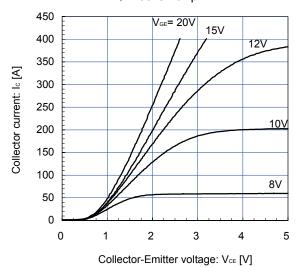
Note \*4: This is the value which is defined mounting on the additional cooling fin with thermal compound.

#### **■** Characteristics (Representative)

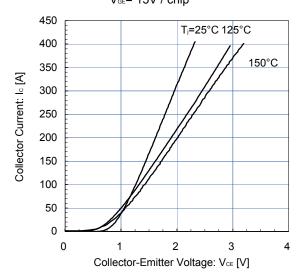
Collector current vs. Collector-Emitter voltage (typ.)  $T_j = 25^{\circ}C$  / chip



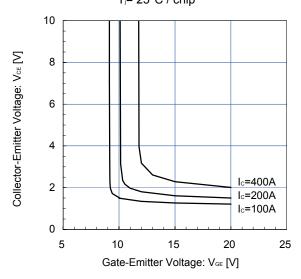
Collector current vs. Collector-Emitter voltage (typ.) T<sub>=</sub> 150°C / chip



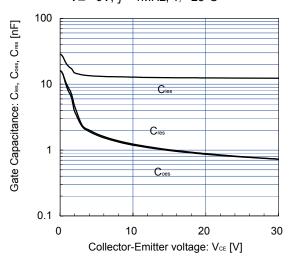
Collector current vs. Collector-Emitter voltage (typ.)  $V_{\text{GE}}$ = 15V / chip



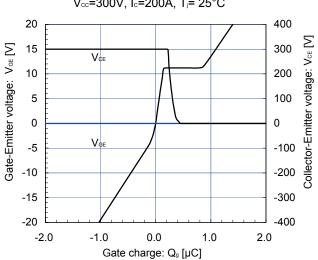
Collector-Emitter voltage vs. Gate-Emitter voltage T<sub>j</sub>= 25°C / chip

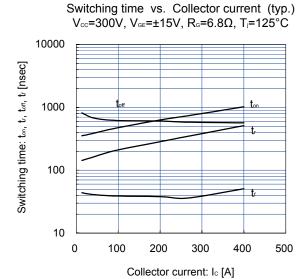


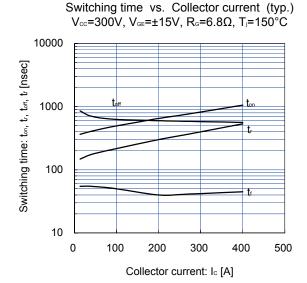
Gate Capacitance vs. Collector-Emitter Voltage  $V_{GE}$ = 0V, f= 1MHz,  $T_{J}$ = 25°C

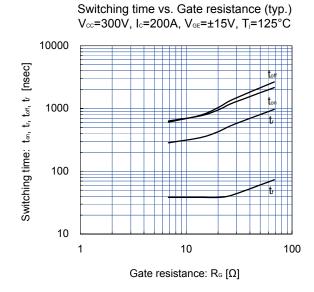


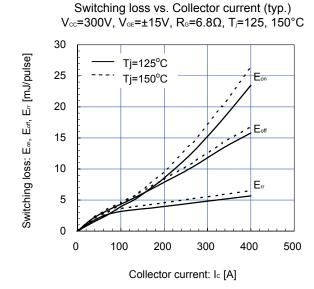
Dynamic Gate Charge (typ.) V<sub>cc</sub>=300V, I<sub>c</sub>=200A, T<sub>i</sub>= 25°C

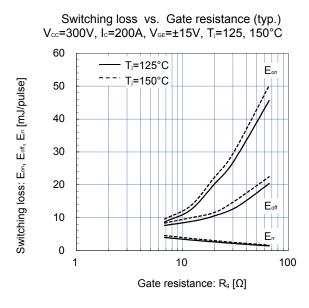


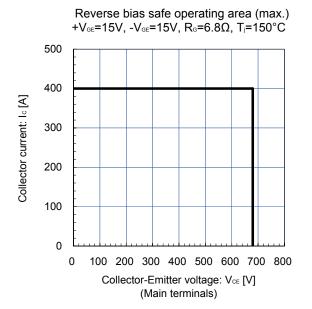




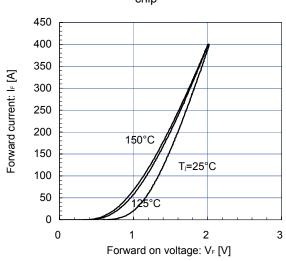




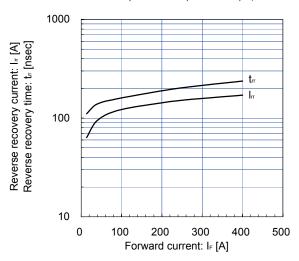




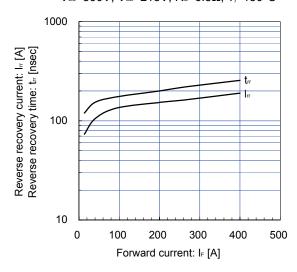
Forward Current vs. Forward Voltage (typ.) chip



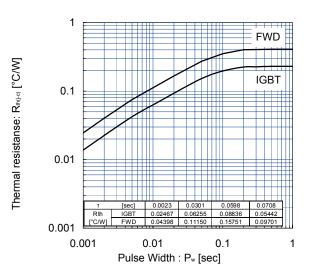
Reverse Recovery Characteristics (typ.)  $V_{\text{CC}}$ =300V,  $V_{\text{GE}}$ =±15V,  $R_{\text{G}}$ =6.8 $\Omega$ ,  $T_{\text{J}}$ =125°C



Reverse Recovery Characteristics (typ.)  $V_{\text{CC}}$ =300V,  $V_{\text{GE}}$ =±15V,  $R_{\text{G}}$ =6.8 $\Omega$ ,  $T_{\text{J}}$ =150°C

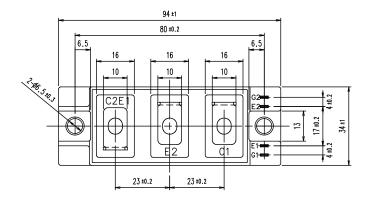


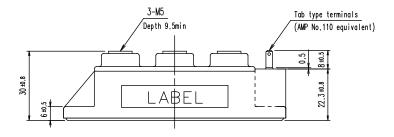
Transient Thermal Resistance (max.)



http://www.fujielectric.com/products/semiconductor/

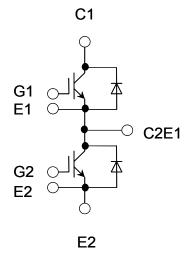
### ■ Outline Drawings, mm





Weight: 180g (typ.)

## **■** Equivalent Circuit Schematic



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